

ABSTRACT OF THE DISCLOSURE

A magnetic random access memory includes a silicon substrate, a transistor which has a gate electrode formed on the silicon substrate via a gate insulating film and diffusion layers formed in the silicon substrate, a first insulating film formed on the silicon substrate and the transistor, a multilayered interconnection formed in the first insulating film, and a magneto-resistive element formed above the first insulating film, wherein at least some of dangling bonds in the silicon substrate are terminated by silicon-deuterium bonds.